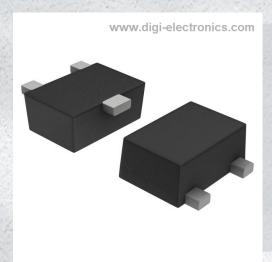


# **NSVDTA143EM3T5G Datasheet**



https://www.DiGi-Electronics.com

DiGi Electronics Part Number NSVDTA143EM3T5G-DG

Manufacturer onsemi

Manufacturer Product Number NSVDTA143EM3T5G

Description TRANS PREBIAS PNP 50V SOT723

Detailed Description Pre-Biased Bipolar Transistor (BJT) PNP - Pre-Biase

d 50 V 100 mA 260 mW Surface Mount SOT-723



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.



## **Purchase and inquiry**

Manufacturer Product Number:	Manufacturer:
NSVDTA143EM3T5G	onsemi
Series:	Product Status:
-	Active
Transistor Type:	Current - Collector (Ic) (Max):
PNP - Pre-Biased	100 mA
Voltage - Collector Emitter Breakdown (Max):	Resistor - Base (R1):
50 V	4.7 kOhms
Resistor - Emitter Base (R2):	DC Current Gain (hFE) (Min) @ Ic, Vce:
4.7 kOhms	15 @ 5mA, 10V
Vce Saturation (Max) @ lb, lc:	Current - Collector Cutoff (Max):
250mV @ 1mA, 10mA	500nA
Power - Max:	Grade:
260 mW	Automotive
Qualification:	Mounting Type:
AEC-Q101	Surface Mount
Package / Case:	Supplier Device Package:
SOT-723	SOT-723
Base Product Number:	
NSVDTA143	

## **Environmental & Export classification**

RoHS Status:	Moisture Sensitivity Level (MSL):
ROHS3 Compliant	1 (Unlimited)
REACH Status:	ECCN:
REACH Unaffected	EAR99
HTSUS:	

8541.21.0095

## Digital Transistors (BRT) R1 = 4.7 k $\Omega$ , R2 = 4.7 k $\Omega$

# PNP Transistors with Monolithic Bias Resistor Network

This series of digital transistors is designed to replace a single device and its external resistor bias network. The Bias Resistor Transistor (BRT) contains a single transistor with a monolithic bias network consisting of two resistors; a series base resistor and a base–emitter resistor. The BRT eliminates these individual components by integrating them into a single device. The use of a BRT can reduce both system cost and board space.

#### **Features**

- Simplifies Circuit Design
- Reduces Board Space
- Reduces Component Count
- S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb–Free, Halogen Free/BFR Free and are RoHS Compliant

#### **MAXIMUM RATINGS** $(T_A = 25^{\circ}C)$

Rating	Symbol	Max	Unit
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Collector–Emitter Voltage	$V_{CEO}$	50	Vdc
Collector Current – Continuous	I <sub>C</sub>	100	mAdc
Input Forward Voltage	V <sub>IN(fwd)</sub>	30	Vdc
Input Reverse Voltage	V <sub>IN(rev)</sub>	10	Vdc

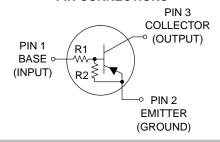
Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

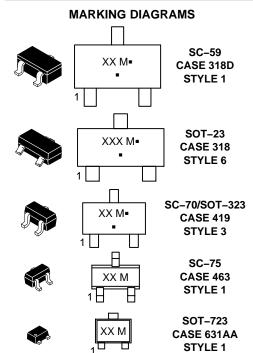


#### ON Semiconductor®

www.onsemi.com

#### **PIN CONNECTIONS**





XXX = Specific Device Code

X ML 1

M = Date Code\*
■ Pb–Free Package

(Note: Microdot may be in either location)

\*Date Code orientation may vary depending upon manufacturing location.

#### **ORDERING INFORMATION**

See detailed ordering, marking, and shipping information in the package dimensions section on page 2 of this data sheet.

SOT-1123

CASE 524AA STYLE 1

**Table 1. ORDERING INFORMATION** 

Device	Part Marking	Package	Shipping <sup>†</sup>
MUN2132T1G, NSVMUN2132T1G*	6J	SC-59 (Pb-Free)	3000 / Tape & Reel
MMUN2132LT1G, NSVMMUN2132LT1G*	A6J	SOT-23 (Pb-Free)	3000 / Tape & Reel
MUN5132T1G, NSVMUN5132T1G*	6J	SC-70/SOT-323 (Pb-Free)	3000 / Tape & Reel
DTA143EET1G	43	SC-75 (Pb-Free)	3000 / Tape & Reel
DTA143EM3T5G, NSVDTA143EM3T5G*	6J	SOT-723 (Pb-Free)	8000 / Tape & Reel
NSBA143EF3T5G	A (90°)*	SOT-1123 (Pb-Free)	8000 / Tape & Reel

<sup>†</sup>For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

<sup>\*\*</sup>  $(xx^\circ)$  = Degree rotation in the clockwise direction.

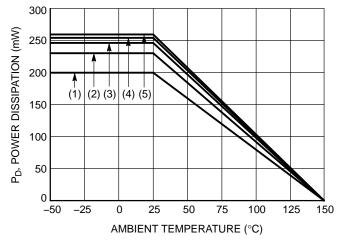


Figure 1. Derating Curve

- (1) SC-75 and SC-70/SOT-323; Minimum Pad
- (2) SC-59; Minimum Pad
- (3) SOT-23; Minimum Pad
- (4) SOT-1123; 100 mm<sup>2</sup>, 1 oz. copper trace
- (5) SOT-723; Minimum Pad

<sup>\*</sup>S and NSV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

**Table 2. THERMAL CHARACTERISTICS** 

	Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTI	CS (SC-59) (MUN2132)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ $\text{(Note 2)}$ Derate above 25°C	(Note 1)	P <sub>D</sub>	230 338 1.8	mW mW/°C
(Note 2) Thermal Resistance,	(Note 1)	$R_{ heta JA}$	2.7 540	°C/W
Junction to Ambient  Thermal Resistance, Junction to Lead (Note 2)	(Note 2)	R <sub>θJL</sub>	370 264 287	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTI		13, 1stg	00 10 1 100	
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 1)  (Note 2)  Derate above 25°C  (Note 2)	(Note 1)	P <sub>D</sub>	246 400 2.0 3.2	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	508 311	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ heta JL}$	174 208	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-70/SOT-323) (MUN5132)	,		
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ $\text{(Note 2)}$ Derate above 25 $^{\circ}$ C $\text{(Note 2)}$	(Note 1)	P <sub>D</sub>	202 310 1.6 2.5	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	618 403	°C/W
Thermal Resistance, Junction to Lead (Note 2)	(Note 1)	$R_{ heta JL}$	280 332	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SC-75) (DTA143EE)			
Total Device Dissipation $T_A = 25^{\circ}C$ (Note 1) (Note 2) Derate above 25°C (Note 2)	(Note 1)	P <sub>D</sub>	200 300 1.6 2.4	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ hetaJA}$	600 400	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C
THERMAL CHARACTERISTI	CS (SOT-723) (DTA143EM3)			
Total Device Dissipation $T_A = 25^{\circ}C \qquad \text{(Note 1)}$ $\text{(Note 2)}$ Derate above $25^{\circ}C$ $\text{(Note 2)}$	(Note 1)	P <sub>D</sub>	260 600 2.0 4.8	mW mW/°C
Thermal Resistance, Junction to Ambient	(Note 1) (Note 2)	$R_{ heta JA}$	480 205	°C/W
Junction and Storage Temper	ature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 2. THERMAL CHARACTERISTICS** 

Characteristic	Symbol	Max	Unit
THERMAL CHARACTERISTICS (SOT-1123) (NSBA143EF3)			
Total Device Dissipation  T <sub>A</sub> = 25°C (Note 3) (Note 4)  Derate above 25°C (Note 3) (Note 4)	P <sub>D</sub>	254 297 2.0 2.4	mW mW/°C
Thermal Resistance, (Note 3) Junction to Ambient (Note 4)	$R_{ hetaJA}$	493 421	°C/W
Thermal Resistance, Junction to Lead (Note 3)	R <sub>θ</sub> JL	193	°C/W
Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	-55 to +150	°C

- 1. FR-4 @ Minimum Pad.
- 2. FR-4 @ 1.0 x 1.0 Inch Pad.
- FR-4 @ 100 mm<sup>2</sup>, 1 oz. copper traces, still air.
   FR-4 @ 500 mm<sup>2</sup>, 1 oz. copper traces, still air.

**Table 3. ELECTRICAL CHARACTERISTICS** (T<sub>Δ</sub> = 25°C, unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS		•			
Collector–Base Cutoff Current $(V_{CB} = 50 \text{ V}, I_E = 0)$	I <sub>CBO</sub>	_	-	100	nAdc
Collector–Emitter Cutoff Current (V <sub>CE</sub> = 50 V, I <sub>B</sub> = 0)	I <sub>CEO</sub>	_	-	500	nAdc
Emitter–Base Cutoff Current (V <sub>EB</sub> = 6.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	_	_	1.5	mAdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 10 μA, I <sub>E</sub> = 0)	V <sub>(BR)</sub> CBO	50	-	-	Vdc
Collector–Emitter Breakdown Voltage (Note 5) (I <sub>C</sub> = 2.0 mA, I <sub>B</sub> = 0)	V <sub>(BR)</sub> CEO	50	_	-	Vdc
ON CHARACTERISTICS	·				
DC Current Gain (Note 5) (I <sub>C</sub> = 5.0 mA, V <sub>CE</sub> = 10 V)	h <sub>FE</sub>	15	27	-	
Collector–Emitter Saturation Voltage (Note 5) (I <sub>C</sub> = 10 mA, I <sub>B</sub> = 1.0 mA)	V <sub>CE(sat)</sub>	_	_	0.25	Vdc
Input Voltage (off) ( $V_{CE} = 5.0 \text{ V}, I_{C} = 100 \mu\text{A}$ )	V <sub>i(off)</sub>	_	1.2	0.5	Vdc
Input Voltage (on) $(V_{CE} = 0.3 \text{ V}, I_C = 20 \text{ mA})$	V <sub>i(on)</sub>	3.0	2.4	-	Vdc
Output Voltage (on) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 2.5 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OL</sub>	_	-	0.2	Vdc
Output Voltage (off) (V <sub>CC</sub> = 5.0 V, V <sub>B</sub> = 0.25 V, R <sub>L</sub> = 1.0 k $\Omega$ )	V <sub>OH</sub>	4.9	-	-	Vdc
Input Resistor	R1	3.3	4.7	6.1	kΩ
Resistor Ratio	R <sub>1</sub> /R <sub>2</sub>	0.8	1.0	1.2	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 5. Pulsed Condition: Pulse Width = 300 msec, Duty Cycle ≤ 2%.

# TYPICAL CHARACTERISTICS MUN2132, MMUN2132L, MUN5132, DTA143EE, DTA143EM3

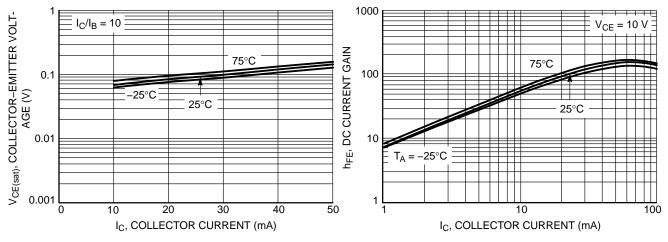


Figure 2. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 3. DC Current Gain

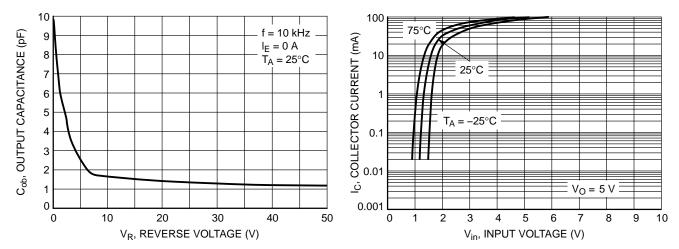


Figure 4. Output Capacitance

Figure 5. Output Current vs. Input Voltage

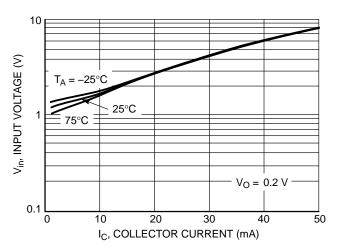


Figure 6. Input Voltage vs. Output Current

#### **TYPICAL CHARACTERISTICS - NSBA143EF3**

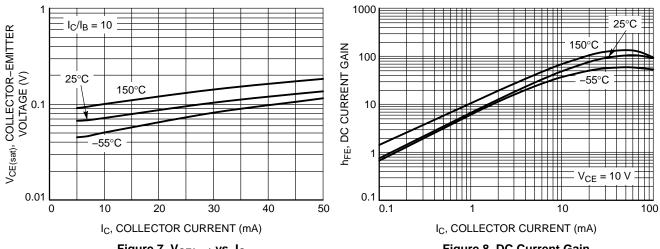


Figure 7. V<sub>CE(sat)</sub> vs. I<sub>C</sub>

Figure 8. DC Current Gain

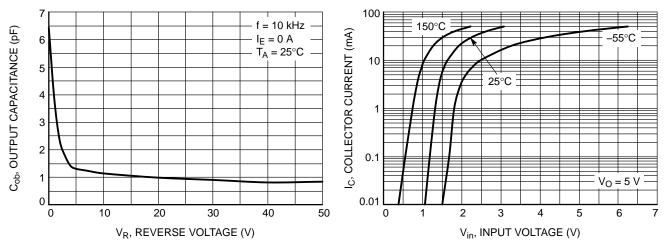


Figure 9. Output Capacitance

Figure 10. Output Current vs. Input Voltage

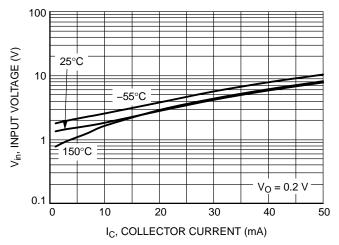


Figure 11. Input Voltage vs. Output Current

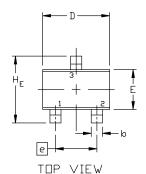


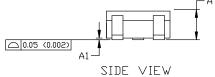
PACKAGE DIMENSIONS

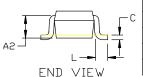
#### SC-70 (SOT-323) **CASE 419** ISSUE R

**DATE 11 OCT 2022** 









#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1982.
- 2. CONTROLLING DIMENSION: INCH

	MILLIMETERS				INCHES	
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.80	0.90	1.00	0.032	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A2		0.70 REF			0.028 BS	C
b	0.30	0.35	0.40	0.012	0.014	0.016
С	0.10	0.18	0.25	0.004	0.007	0.010
D	1.80	2.00	2.20	0.071	0.080	0.087
E	1.15	1.24	1.35	0.045	0.049	0.053
е	1.20	1.30	1.40	0.047	0.051	0.055
e1	0.65 BSC				0.026 BS	C
L	0.20	0.38	0.56	0.008	0.015	0.022
HE	2.00	2.10	2.40	0.079	0.083	0.095

#### **GENERIC MARKING DIAGRAM**

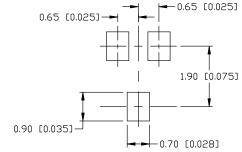


XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.



For additional information on our Pb-Free strategy and soldering details, please download the ID Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

SOLDERING FOOTPRINT

STYLE 1: CANCELLED	STYLE 2: PIN 1. ANODE 2. N.C. 3. CATHODE	STYLE 3: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 5: PIN 1. ANODE 2. ANODE 3. CATHODE	
STYLE 6:	STYLE 7:	STYLE 8:	STYLE 9:	STYLE 10:	STYLE 11:
PIN 1. EMITTER	PIN 1. BASE	PIN 1. GATE	PIN 1. ANODE	PIN 1. CATHODE	PIN 1. CATHODE
2. BASE	2. EMITTER	2. SOURCE	2. CATHODE	2. ANODE	<ol><li>CATHODE</li></ol>
<ol><li>COLLECTOR</li></ol>	<ol><li>COLLECTOR</li></ol>	3. DRAIN	<ol><li>CATHODE-ANODE</li></ol>	3. ANODE-CATHODE	<ol><li>CATHODE</li></ol>

DOCUMENT NUMBER:	98ASB42819B	Electronic versions are uncontrolled except when accessed directly from the Document R- Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.		
DESCRIPTION:	SC-70 (SOT-323)		PAGE 1 OF 1	

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**PACKAGE DIMENSIONS** 

#### SC75-3 1.60x0.80x0.80, 1.00P

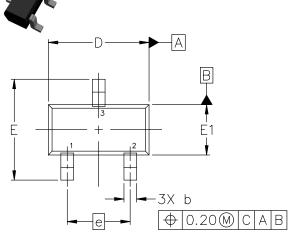
**CASE 463 ISSUE H** 

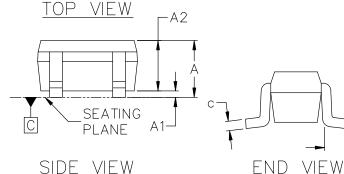
**DATE 01 FEB 2024** 

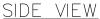
#### NOTES:

- DIMENSIONING AND TOLERANCING CONFORM TO ASME Y14.5-2018.
- ALL DIMENSION ARE IN MILLIMETERS.

DIM	М	MILLIMETERS				
UIIVI	MIN.	NOM.	MAX.			
А	0.70	0.80	0.90			
A1	0.00	0.05	0.10			
A2	0.80 REF.					
b	0.15	0.20	0.30			
С	0.10	0.15	0.25			
D	1.55	1.60	1.65			
Е	1.50	1.60	1.70			
E1	0.70	0.80	0.90			
е	1.00 BSC					
L	0.10	0.15	0.20			







#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code

Μ = Date Code

= Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 2:

STYLE 1:	
PIN 1. BASE	
2. EMITTER	

PIN 1. ANODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

RECOMMENDED MOUNTING FOOTPRINT\* FOR ADDITIONAL INFORMATION ON OUR Pb-FREE STRATEGY AND SOLDERING DETAILS, PLEASE DOWNLOAD THE ON SEMICONDUCTOR SOLDERING AND MOUNTING TECHNIQUES

REFERENCE MANUAL, SOLDERRM/D.

2. EMITTER	2. N/C
3. COLLECTOR	3. CATHODE
STYLE 4:	STYLE 5:
PIN 1. CATHODE	PIN 1. GATE
2. CATHODE	<ol><li>SOURCE</li></ol>
3. ANODE	<ol><li>DRAIN</li></ol>

DOCUMENT NUMBER:	98ASB15184C	Electronic versions are uncontrolled except when accessed directly from Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SC75-3 1.60x0.80x0.80, 1.00P		PAGE 1 OF 1

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## PACKAGE DIMENSIONS

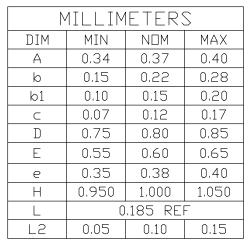


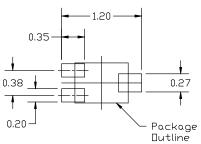
#### SOT-1123 0.80x0.60x0.37, 0.35P CASE 524AA ISSUE D

**DATE 18 JAN 2024** 

#### NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS. 2.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

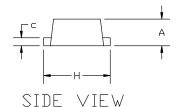


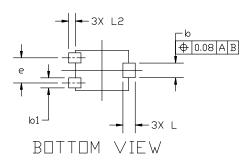


#### RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference manual, SOLDERRM/D.

# В ТПР VIEW





#### **GENERIC MARKING DIAGRAM\***



= Specific Device Code

= Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1:			
PIN 1. BASE			
2. EMITTER			
3 COLLECTOR			

STYLE 2: PIN 1. ANODE 2. N/C 3. CATHODE

STYLE 3: PIN 1. ANODE 2. ANODE 3. CATHODE

STYLE 4: PIN 1. CATHODE 2. CATHODE 3. ANODE

STYLE 5: PIN 1. GATE 2. SOURCE

DOCUMENT NUMBER:	98AON23134D	Electronic versions are uncontrolled except when accessed directly fron Printed versions are uncontrolled except when stamped "CONTROLLED	
DESCRIPTION:	SOT-1123 0.80x0.60x0.37, 0.35P		PAGE 1 OF 1

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PACKAGE DIMENSIONS

MILLIMETERS

 $N\square M$ .

0.50

0.21

0.31

0.12

1.20

0.80

0.40 BSC

1.20

0.29 REF



#### SOT-723 1.20x0.80x0.50, 0.40P CASE 631AA ISSUE E

**DATE 24 JAN 2024** 

MAX.

0.55

0.27

0.37

0.17

1.25

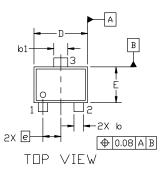
0.85

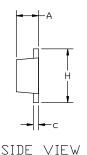
1.25

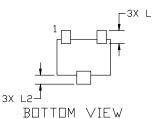
0.25

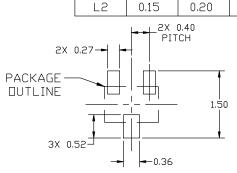
#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.









DIM

Α

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b1

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е Н

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MIN.

0.45

0.15

0.25

0.07

1.15

0.75

1.15

#### RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

#### **GENERIC MARKING DIAGRAM\***



XX = Specific Device Code = Date Code

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: STYLE 2: STYLE 3: STYLE 4: STYLE 5: PIN 1. GATE 2. SOURCE PIN 1. BASE PIN 1. ANODE PIN 1. ANODE PIN 1. CATHODE 2 FMITTER 2 CATHODE 2 N/C 2. ANODE 3. COLLECTOR 3. CATHODE 3. CATHODE 3. DRAIN

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DESCRIPTION:	SOT-723 1.20x0.80x0.50, 0.40P		PAGE 1 OF 1

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